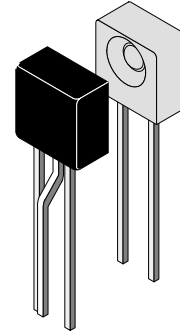


## Matchable Pairs – Emitter and Detector

### Description

Pairs of infrared-emitting diode and photologic detector, matched in their optical and electrical features. These pairs enable a lot of applications. They can be used both for transmissive or reflective sensor functions. The peak wavelength of the emitter is  $\lambda = 950 \text{ nm}$ . The detector consists of a photologic IC with Schmitt trigger and open collector output.



96 12366

### Applications

- Detection of opaque material, documents etc
- Paper position sensor in copy machines
- Position sensor for shaft encoder

### Features

- Output level 'LOW' when infrared beam is not interrupted
- TTL compatible
- Small dimensions
- Detector provided with daylight filter
- Emitter and detector in side view case
- Miniature plastic case with lens
- Operating angle  $\pm \varphi = 35^\circ$

### Handling Precautions

Connect a capacitor C of 100 nF between  $V_{S1}$  and ground in order to stabilize power supply voltage!

### Order Instruction

Ordering Code	Remarks
TCZS8100-PAER	

### Absolute Maximum Ratings

#### Input (Emitter)

Parameter	Test Conditions	Symbol	Value	Unit
Reverse voltage		$V_R$	6	V
Forward current		$I_F$	60	mA
Forward surge current	$t_p \leq 10$ s	$I_{FSM}$	3	A
Power dissipation	$T_{amb} \leq 25$ °C	$P_V$	100	mW
Junction temperature		$T_j$	100	°C

#### Output (Detector)

Parameter	Test Conditions	Symbol	Value	Unit
Supply voltages range		$V_{S1}$	-0.5 to +16	V
		$V_{S2}$	20	V
Output current		$I_O$	20	mA
Power dissipation	$T_{amb} \leq 85$ °C	$P_V$	50	mW
Junction temperature		$T_j$	100	°C

#### Emitter and Detector matched

Parameter	Test Conditions	Symbol	Value	Unit
Ambient temperature range		$T_{amb}$	-25 to +85	°C
Storage temperature range		$T_{stg}$	-40 to +100	°C
Soldering temperature	2 mm from case, $t \leq 5$ s	$T_{sd}$	260	°C

**Note:** Operating conditions are stabilized after 100  $\mu$ s of supply voltage turn on.

### Electrical Characteristics ( $T_{amb} = 25$ °C)

#### Input (Emitter)

Parameter	Test Conditions	Symbol	Min.	Typ.	Max.	Unit
Forward voltage	$I_F = 50$ mA	$V_F$		1.25	1.65	V
Junction capacitance	$V_R = 0$ , $f = 1$ MHz	$C_j$		50		pF

#### Output (Detector)

Parameter	Test Conditions	Symbol	Min.	Typ.	Max.	Unit
Supply voltage range		$V_{S1}$	4.5		16	V

#### Emitter and Detector matched <sup>1)</sup>

Parameter	Test Conditions	Symbol	Min.	Typ.	Max.	Unit
Supply current	$V_{S1} = 16$ V	$I_{s1}$		3	5	mA
Output current	$V_{S1} = V_{S2} = 16$ V, $I_F = 0$	$I_{OH}$			1	$\mu$ A
Input threshold current	$V_{S1} = 5$ V	$I_{FT}$		3	10	mA
Hysteresis	$V_{S1} = 5$ V	$I_{Foff}/I_{Fon}$		80		%
Output voltage	$I_{OL} = 16$ mA, $I_F > I_{FT}$ , $V_{S1} = 5$ V			0.15	0.4	V
Switching frequency	$I_F = 3 \times I_{FT}$ , $R_L = 1$ k $\Omega$ , $V_{S1} = V_{S2} = 5$ V	$f_{sw}$		200		KHz

<sup>1)</sup> Characteristics are measurement at a separation distance of 4 mm (1.55") within a common axis of 0.5 mm (0.02") and parallel within 5°

## Switching Characteristics

Parameter	Test Conditions	Symbol	Typ.	Unit
Rise time	$V_{S1} = V_{S2} = 5\text{ V}$ , $I_F = 3 \times I_{FT}$ , $R_L = 1\text{ k}\Omega$ (see figure 1)	$t_r$	50.0	ns
Turn-on time		$t_{on}$	1.0	$\mu\text{s}$
Fall time		$t_f$	20.0	ns
Turn-off time		$t_{off}$	3.0	$\mu\text{s}$

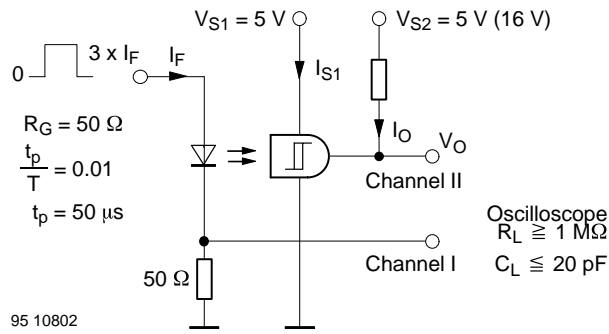


Figure 1. Test circuit

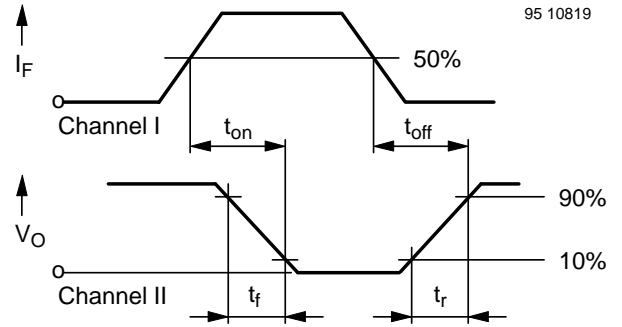


Figure 2. Pulse diagram

### Typical Characteristics ( $T_{amb} = 25^{\circ}\text{C}$ , unless otherwise specified)

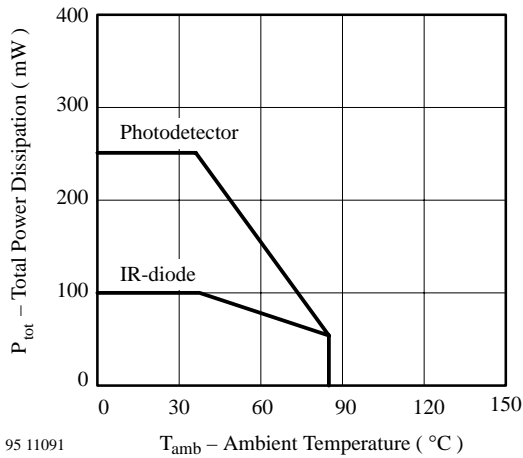


Figure 3. Total Power Dissipation vs. Ambient Temperature

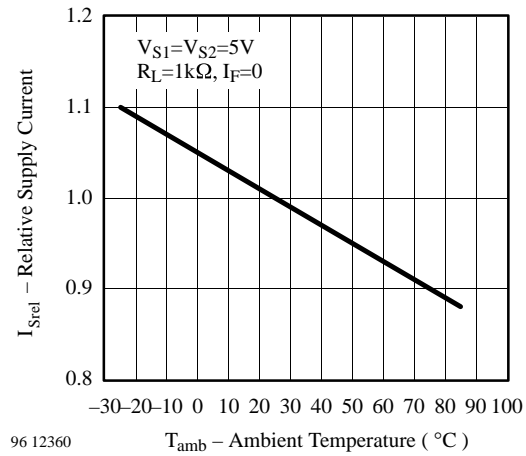


Figure 6. Relative Supply Current vs. Ambient Temperature

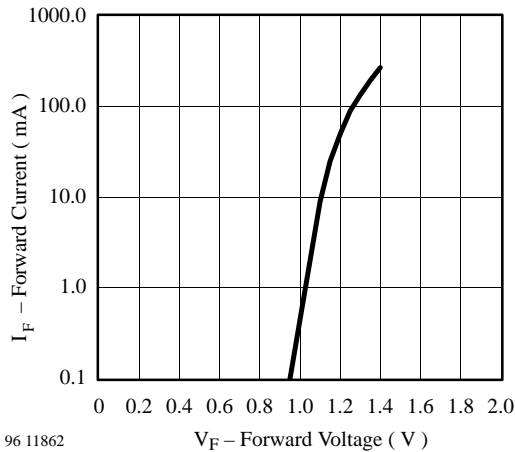


Figure 4. Forward Current vs. Forward Voltage

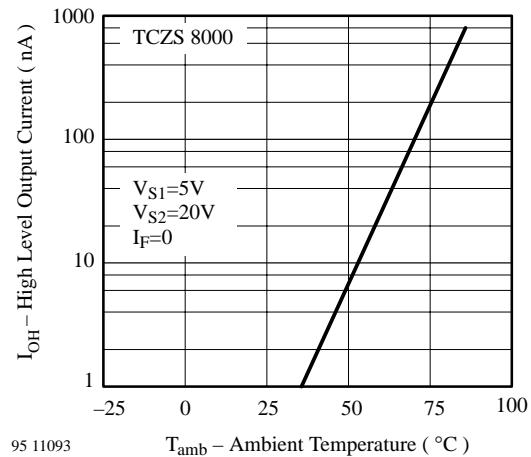


Figure 7. High Level Output Current vs. Ambient Temperature

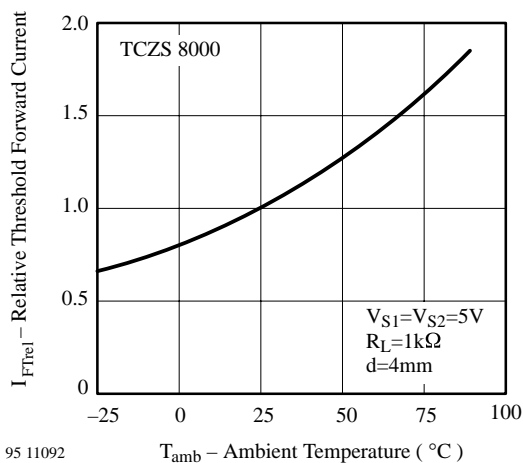
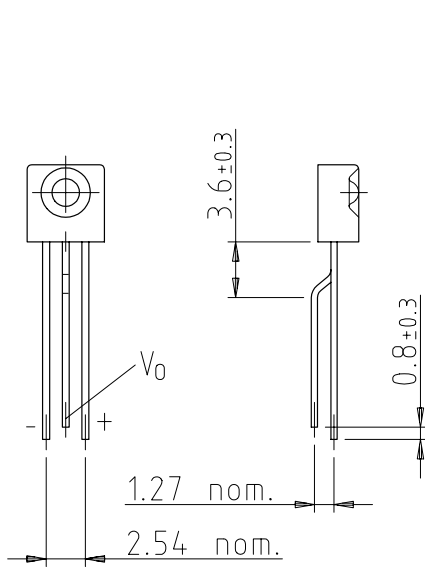
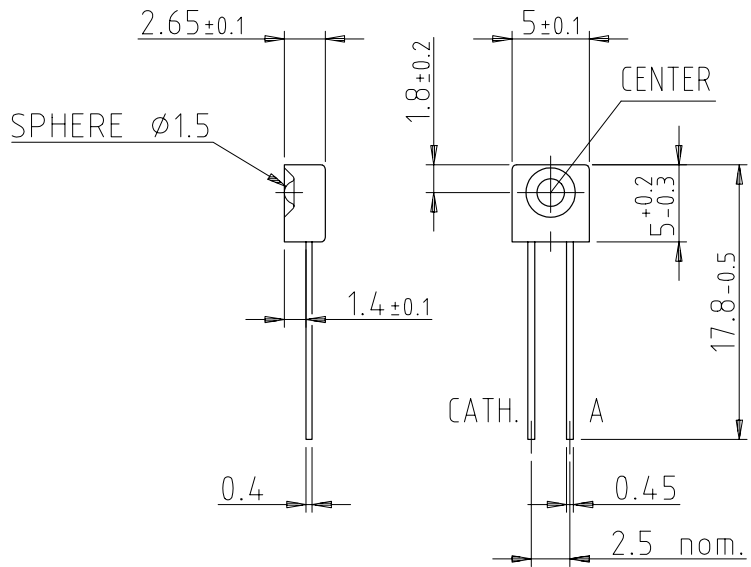


Figure 5. Relative Threshold Forward Current vs. Ambient Temperature

**Dimensions of TCZS8100 in mm**

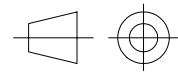


DETECTOR (BLACK)  
 ( MISSING DIM. SEE EMITTER )



EMITTER (CLEAR)

weight: ca. 0.25g



technical drawings  
 according to DIN  
 specifications

9 6 12104

### Ozone Depleting Substances Policy Statement

It is the policy of **Vishay Semiconductor GmbH** to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

**Vishay Semiconductor GmbH** has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

**Vishay Semiconductor GmbH** can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

**We reserve the right to make changes to improve technical design and may do so without further notice.**

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Telefunken products for any unintended or unauthorized application, the buyer shall indemnify Vishay Telefunken against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

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